

ABSTRACT

The present application provides an epitaxial silicon wafer and a manufacturing method therefor. During an epitaxial layer growth process, steps of growing a homoepitaxial layer in sequential stages on one side of a substrate material includes: providing a substrate silicon wafer; depositing an intermediate epitaxial layer on the substrate silicon wafer, and then performing an edge profile flatness compensation on the intermediate epitaxial layer; depositing a top epitaxial layer on the intermediate epitaxial layer; the method includes at least one first stage and one second stage.

(Figure 6)